

Part Number

Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	439.00 +/- 11.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Flatness (SBIR)	<1.00um	20mm x 20mm, no partials, b/side ref, 100% UA
	8.0	Bow	<60.00µm	ADE to ASTM F534
	9.0	Warp	<60.00µm	ADE to ASTM F657
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	14.0	Handle Thickness	420.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorous	Wafer Vendor
	17.0	Handle Resistivity	0.01 – 0.1 Ohm-cm	Wafer Vendor
	18.0	Backside Finish	Polished with light handling marks, oxide and laser mark.	
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	24.0	Nominal Thickness	18.00 +/- 0.50 µm	Filmetrics, 100% 9-Pt (note3)
	25.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phosphorous	Wafer Vendor
	28.0	Device Resistivity	0.01 – 0.02 Ohm-cm	Wafer Vendor
	29.0	Voids	0	Bright Light, 100% (note 2)
	30.0	Scratches	none	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)
	32.0	LPD Count	<30 @ 0.3um	Tencor Particle Counter

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information